

DRW

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Application of:

Shang-Chih Chen

Group Art Unit: 2826

Serial No.: 10/809,974

Examiner: Quach, Tuan N.

Filed: March 26, 2004

In Response to Office Action

Dated: Feb. 14, 2005

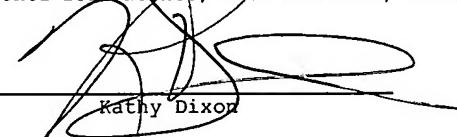
For: High-K Gate Dielectric Stack with Buffer Layer to Improve
Threshold Voltage Characteristics

Attorney Docket No.: 67,200-1258

Certificate of Mailing

I hereby certify that this paper is being deposited with the United States Postal Service on the date shown below with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Date: Mar. 11 2005


Kathy Dixon

RESPONSE TO OFFICE ACTION

Commissioner for Patents
Alexandria, VA 22313-1450

Dear Sir:

In response to an Office Action mailed Feb. 14, 2005 of a restriction requirement imposed by the Examiner, the Applicants hereby elect with traverse the prosecution of Group II, device claims 22-40.